

Analysis of barrier inhomogeneities of P-type Al/4H-SiC Schottky barrier diodes

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Analysis of deep level centers in GaAs pin-diode structures

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Change in the parameters of electron-irradiated 4H-SiC Schottky diodes as a function of the time during low-temperature isothermal annealing

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Comparative characteristics of diffusion-welded high-voltage stacks and connected in series Schottky diodes

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Comparative investigation of the graphene-on-silicon carbide and CVD graphene as a basis for biosensor application

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Comparative results of low temperature annealing of lightly doped n-layers of silicon carbide irradiated by protons and electrons

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Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0.9 MeV electrons

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Investigation of the graphene-on-silicon-carbide and CVD graphene as a basis for bioimpedance sensor applications : poster

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Low-temperature annealing of lightly doped n-4H-SiC layers after irradiation with fast electrons

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Method of samples preparation intended for research of deep centers in i-, n-, and p-layers of GaAs p⁺-pin-n⁺ structures and result of analysis

Toompuu, Jana; **Sleptšuk, Natalja**; **Korolkov, Oleg**; **Rang, Toomas** BEC 2016 : 2016 15th Biennial Baltic Electronics Conference : proceedings of the 15th Biennial Baltic Electronics Conference : Tallinn University of Technology, October 3-5, 2016, Tallinn, Estonia 2016 / p. 35-38 : ill http://www.ester.ee/record=b2150914*est

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